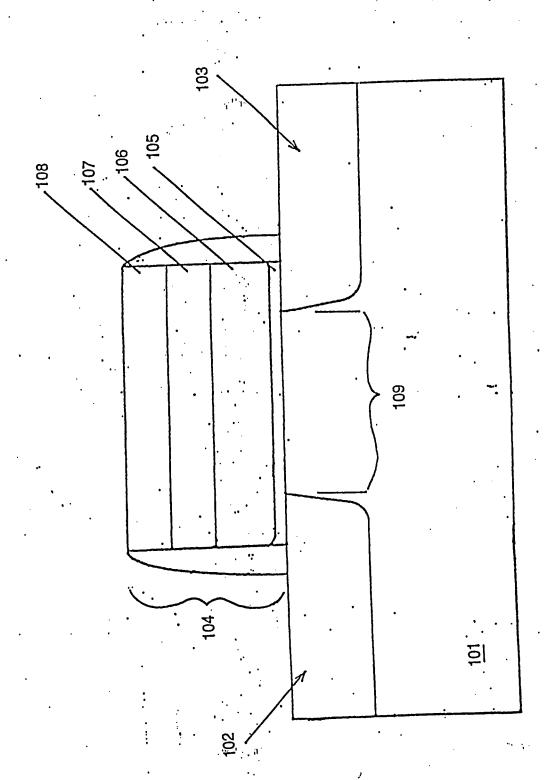
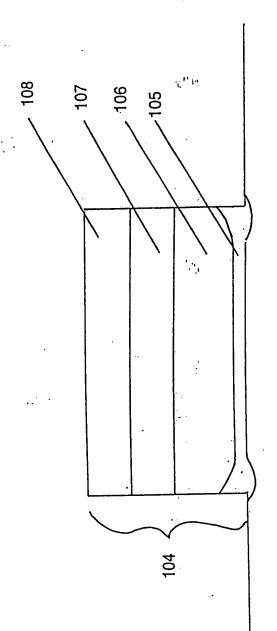
FIGURE 1 (PRIOR ART)



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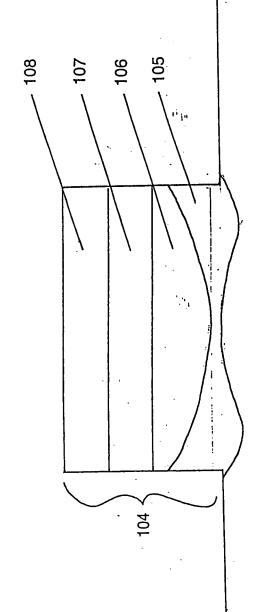
FIGURE 2 (PRIOR ART)



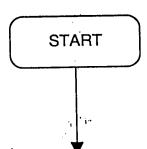
200

STAEDTLER° No. 93, 811E Engineer's Computation Pad

FIGURE 3 (PRIOR ART)



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FABRICATING A GATE STRUCTURE COMPRISING A TUNNEL OXIDE LAYER, A FLOATING GATE LAYER, AN OXIDE LAYER, AND A CONTROL GATE LAYER UPON A SEMICONDUCTOR SUBSTRATE

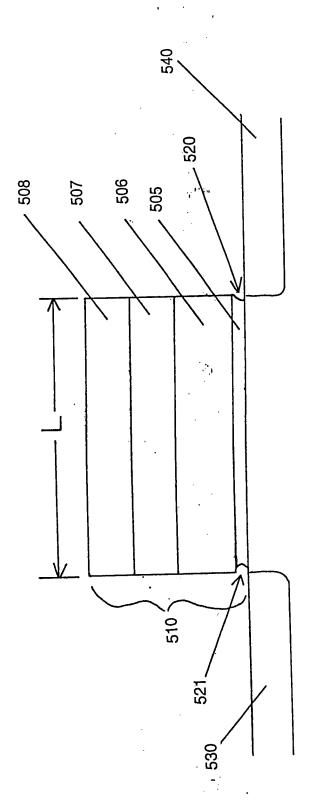
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REPAIRING THE TUNNEL OXIDE LAYER USING A RAPID THERMAL OXIDATION PROCESS

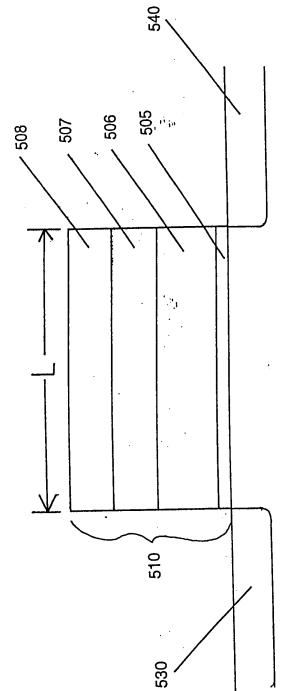
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END

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